IN THE SPECIFICATION:

Please replace the paragraph at page 25, ln. 20 - page 26, ln. 22 with the following amended paragraph:

Subsequently, a barrier 111 for covering the end portions of the anode 110 is formed (FIG. 1A). The barrier 111 is formed in order to keep the insulation between the pixels which are adjacently located from each other and from the wirings by covering a contact hole of a TFT and the wiring 109. For the barrier 111, an inorganic material (silicon oxide, silicon nitride, silicon oxide nitride and the like), a photosensitive or non-photosensitive organic material (Polyimide, acryl, polyamide, polyimide, polyimide amide, resist or benzocyclobutene), or a laminated layer of these and the like can be used, however, herein, a negative type photosensitive acryl is used. A negative type organic resin which is not to be dissolved in an etchant by exposing it to the light is used, a curved surface having the first curvature radius is made at the upper end portion of the barrier and a curved surface having the second curvature radius is made at the lower end portion of the barrier. It is preferable that the foregoing first curvature radius and the foregoing second curvature radius are made in the range from 0.2 μm to 3 μm. Moreover, in the case where a positive-type organic resin which is to be dissolved in an etchant by exposing it to the light is used, the curved surface having a curvature radius can be made only at the upper end of the barrier. The non-light emitting region generated immediately after the light emitting element has been fabricated is not to be generated by making the curved surface have a radius of curvature at the upper end portion of the barrier or at the lower end portion of the barrier.

Please replace the paragraph at page 46, ln. 24 - page 48, ln. 4 with the following amended paragraph:

Moreover, poly (ethylenedioxythiophene)/poly (styrene sulfonic acid) aqueous solution (PEDOT/PSS), polyaniline/camphor sulfonic acid aqueous solution (PANI/CSA), PTPDES, Et-PTPDEK, PPBA or the like which will act as a hole injection layer (anode buffer layer) may be coated and baked on the first electrode (anode) 28a. In the case where a hole injection layer composed of a high-molecular weight material formed by a coating method using a spin coat and the like was formed, the surface flatness is enhanced, the coverage and film thickness uniformity of the film formed on the hole injection layer can be made excellent. Particularly, a uniform light emission can be obtained since the film thickness of the light emitting layer becomes uniform. In this case, after the hole injection layer has been formed by a coating method, it is preferable that the vacuum heating (100 to 200° C) is carried out prior to the formation of the film by a vapor deposition method. It should be noted that an example of a flow chart of the steps concerning this case is shown in FIG. 6. For example, after the surface of the first electrode (anode) has been washed with a sponge, the formation of a light emitting layer is performed by a vapor deposition method without being in contact with the atmospheric air by temporarily baking poly (~~ethyleneoxythiophene~~ ethylenedioxythiophene)/poly(styrene sulfonic acid) aqueous solution (PEDOT/PSS) in a thickness of 60 nm at 80° C for 10 minutes by a spin coat method, fully baking at 200° C for one hour, and further, performing the vacuum heating (170° C, heating for 30 minutes, cooling 30 minutes) on the entire surface of it. Particularly, in the case where convex portions and concave portions, and minute grains exist on the surface of ITO film, these influences can be reduced by making the film thickness of PEDOT/PSS slightly thicker.